

**I2C Real-Time Clock/ Calendar with 5µAh Integrated Backup Power**

**Features**

- Integrated rechargeable solid state battery with power-fail detect and automatic switchover, providing greater than 24 hours of RTC backup
- Smallest commercially available RTC with integrated backup power in compact 5mm x 6mm 1.4mm QFN package
- Temperature compensated charge control
- Integrated EnerChip™ recharged at VDD > 2.5V
- SMT - lead-free reflow tolerant
- Real time clock provides year, month, day, week-day, hours, minutes, and seconds based on a 32.768 kHz quartz crystal
- Resolution: seconds to years
- Watchdog functionality
- Freely programmable timer and alarm with interrupt capability
- 2-line I2C-bus with separate, but combinable data input and output
- Selectable integrated oscillator load capacitors for  $C_L = 7 \text{ pF}$  or  $C_L = 12.5 \text{ pF}$
- Internal Power-On Reset (POR)
- Open-drain interrupt and clock output pins
- Programmable offset register for frequency adjustment
- Eco-friendly, RoHS compliant - tested

**Applications**

- Wireless sensors and RFID tags
- Power Bridging
- Consumer appliances
- Business and industrial systems
  - (A) Time keeping application
  - (B) Battery powered devices
  - (C) Metering
  - (D) High duration timers
  - (E) Daily alarms
  - (F) Low standby power applications

**Part Numbering Example: CCBC34523 T- A5**

CCBC34523	T	Q5C	A5
SERIES	SHIPPING PKG	PACKAGE STYLE	OPERATING TEMP.
	T = Tube Z1 = 1K Z5 = 5K	Q5C = 16-pin QFN	-20°C to +70°C

**Electrical Properties**

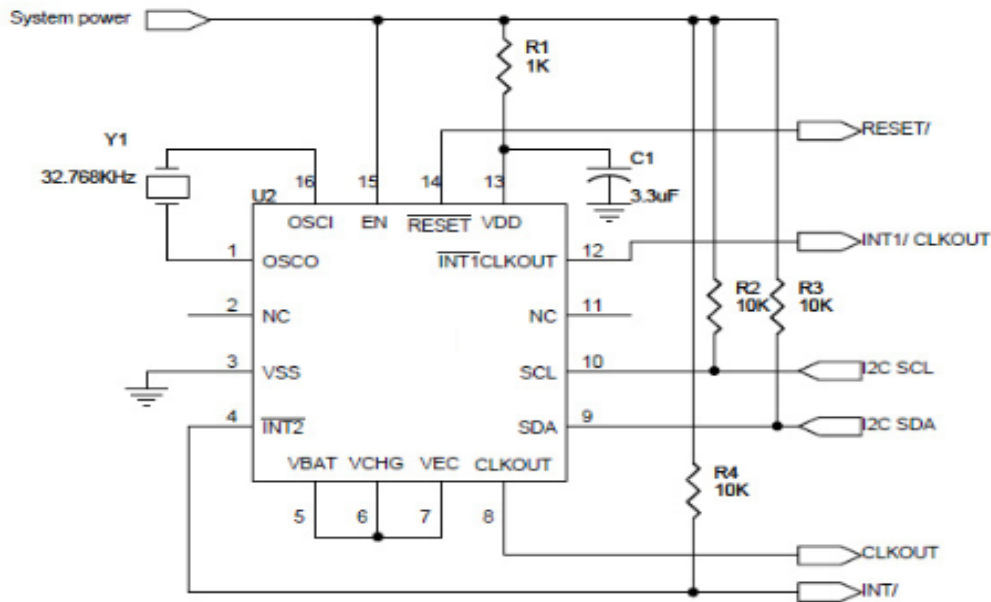
Minimum VDD to Charge EnerChip:	2.5V
Energy Capacity (typical):	5µAh
Recharge time to 80%:	10 minutes
Charge/ Discharge cycles:	>5000 to 10% depth-of-discharge

**Physical Properties**

Package size:	5mm x 5mm x 1.4mm
Operating temperature:	-20°C to +70°C
Storage temperature:	-40°C to +125°C



5mm x 6mm x 1.4mm 16-QFN Package



**Figure 1: CCBC34523 Pin-out Diagram**

### General Description

The EnerChip™ RTC CBC34523-Q5C combines a Real-Time Clock (RTC) and calendar optimized for low power applications with an integrated rechargeable solid state backup power source and all power management functions. The EnerChip™ RTC ensures a seamless transition from main power to backup power in the event of power loss. The integrated power management circuit provides thousands of charge-discharge cycles from the integrated EnerChip™ and manages battery charging, discharge cutoff, power switchover, and temperature compensation to maximize the service life of the device. The CCBC34523 provides greater than 24 hours of backup time in the event main power is interrupted. Typical blackout times are less than 4 hours. The EnerChip™ has extremely low self-discharge, recharges quickly, is non-flammable, and RoHS-compliant. The EnerChip™ is charged automatically anytime VDD is above 2.5V.

Data is transferred serially via an I2C-bus with a maximum data rate of 1000 Knits/s. Alarm and timer functions provide the option to generate a wake-up signal on an interrupt pin. An offset register allows fine tuning of the clock.

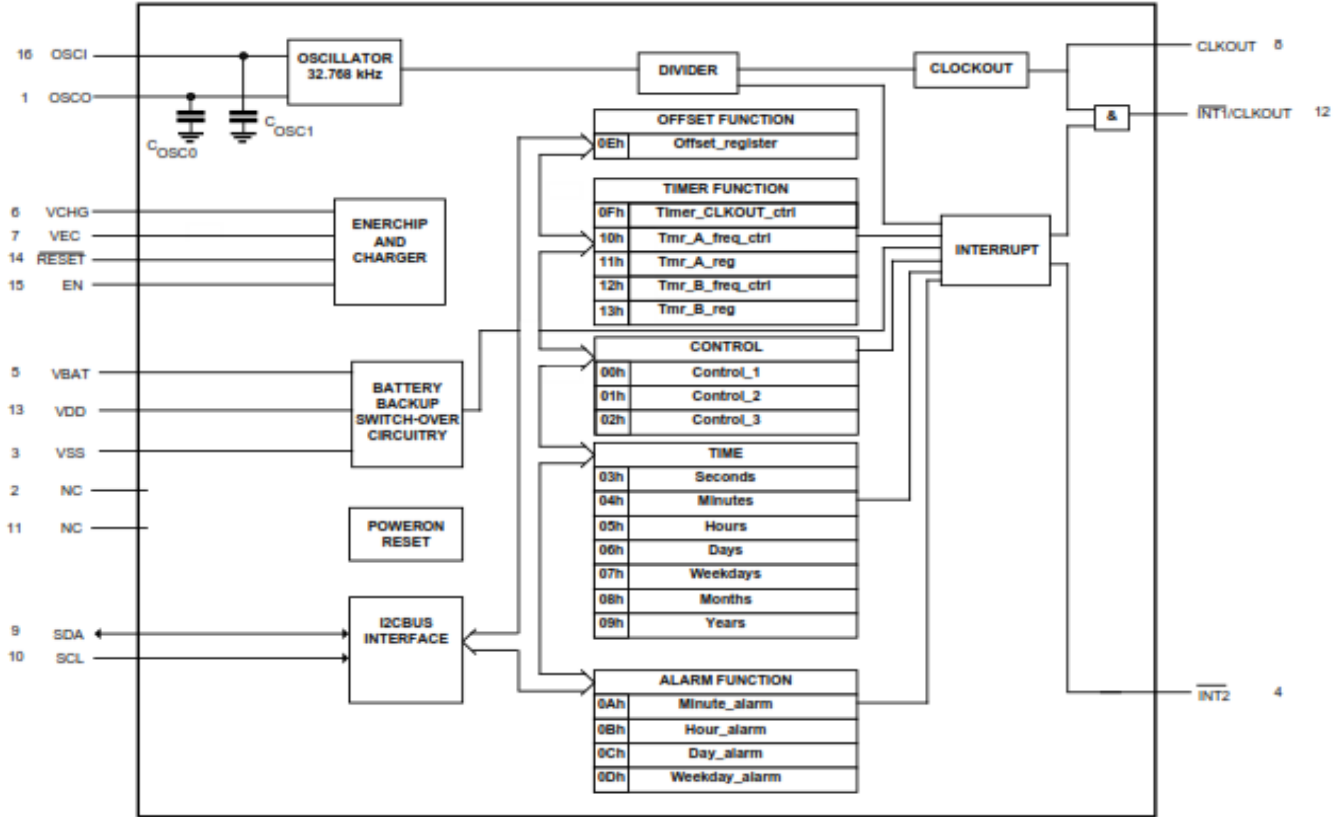


Figure 2: CCBC34523 Block Diagram with Registers

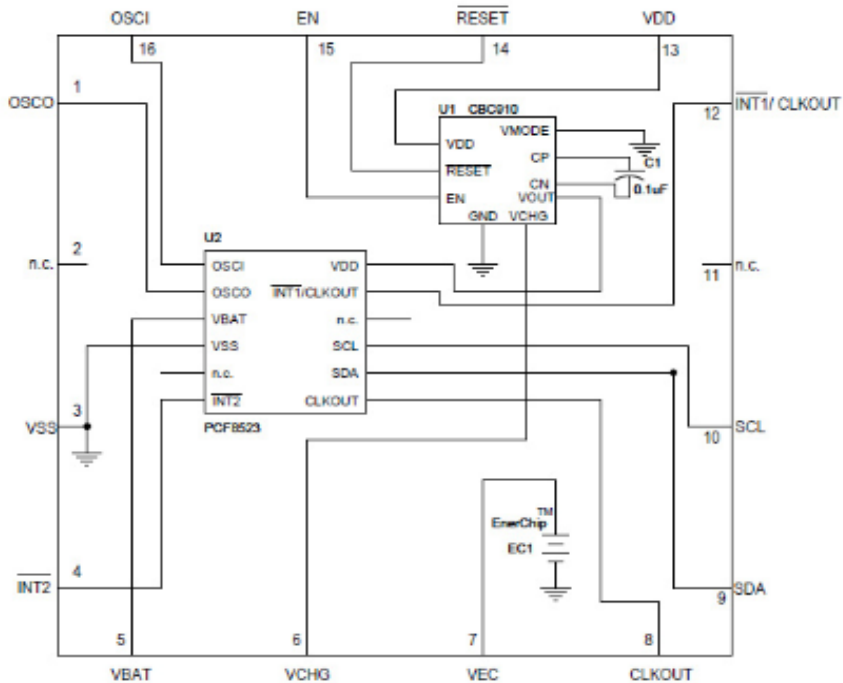


Figure 3: Internal Schematic of CBC34523 EnerChip™ RTC

**CCBC34523-RTC Input/Output Descriptions**

Pin Number	Label	Description
1	OSCO	Oscillator output; high-impedance node; minimize wire length between quartz and package
2	NC	Not connected; do not connect and do not use it as feed through
3	VSS	Ground
4	INT2/	Interrupt 2 output (open-drain; active LOW)
5	VBAT	Backup battery supply input
6	VCHG	4.1V (typical) charging source - connect to VBAT only, or VBAT and optional EnerChip(s)
7	VEC	Positive terminal of integrated thin film battery - connect to VCHG and nothing else
8	CLKOUT	Clock output (open-drain)
9	SDA	Serial data Input/output
10	SCL	Serial clock Input
11	NC	Not connected; do not connect and do not use it as feed through
12	INT1/ CLKOUT/	Interrupt 1 / clock output (open-drain)
13	VDD	Supply voltage
14	RESET/	Output signal indicating RTC is operating in backup power mode
15	EN	Charge pump enable; activates VCHG 4.1V (typ.) charging source
16	OSCI	Oscillator Input; high-impedance node; minimize wire length between quartz and package

**Package Dimensions**

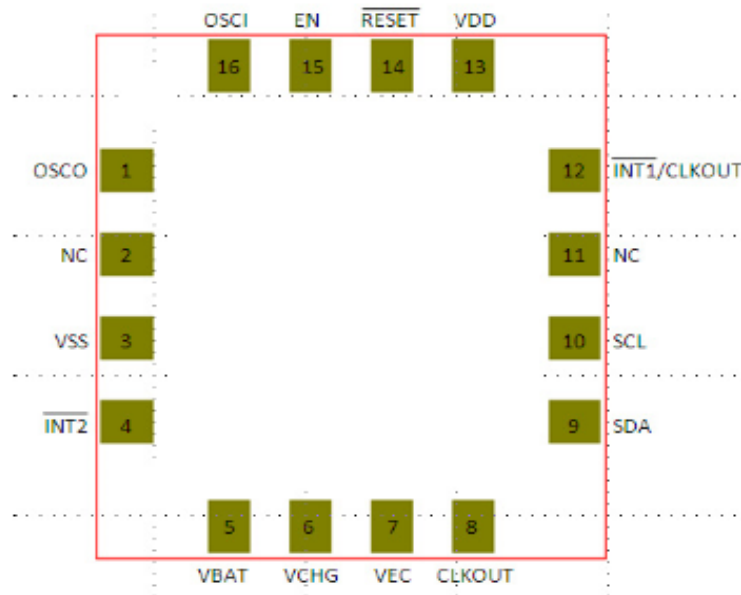
5mm x 6mm x 1.4mm

**Pad Pitch**

0.8mm

**Pad Dimensions**

0.4mm x 0.3mm


**Figure 4: CCBC34523 EnerChip™ RTC Package Pin-Out (top view, looking through package)**

**Absolute Maximum Ratings**

PARAMETER	CONDITION	MIN	TYPICAL	MAX	UNITS
VDD with respect to GND	25 °C	GND - 0.3	-	6.0	V
ENABLE Input Voltage	25 °C	GND - 0.3	-	VDD+0.3	V
VBAT <sup>(1)</sup>	25 °C	3.0	-	4.15	V
VCHG <sup>(1)</sup>	25 °C	3.0	-	4.15	V
RESET Output Voltage	25 °C	GND - 0.3	-	VOUT+0.3	V
CP, Flying Capacitor Voltage	25 °C	GND - 0.3	-	6.0	V
CN	25 °C	GND - 0.3	-	VDD+0.3	V

(1) No external connections to these pins are allowed, except parallel EnerChips™.

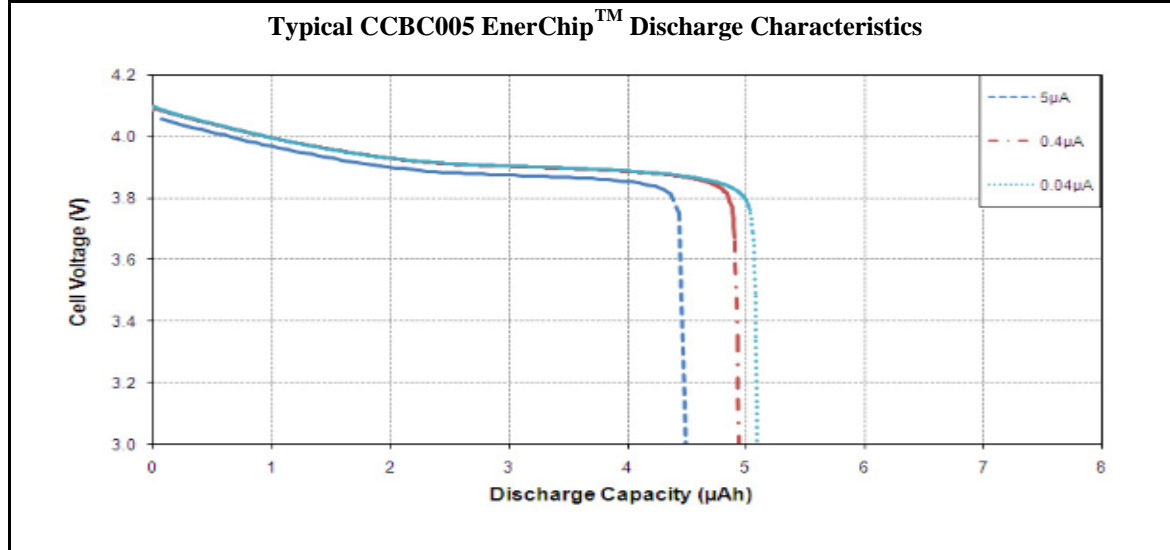
**Integrated EnerChip™ Thin Film Battery Operating Characteristics**

PARAMETER	CONDITION	MIN	TYPICAL	MAX	UNITS	
Self-Discharge (5 yr. average)	Non-recoverable	-	2.5	-	% per year	
	Recoverable	-	1.5 <sup>(1)</sup>	-	% per year	
Operating Temperature	-	-20	25	+70	°C	
Storage Temperature	-	-40	-	+125 <sup>(2)</sup>	°C	
Recharge Cycles (to 80% of rated capacity)	25 °C	10% depth-of-discharge	5000	-	-	cycles
		50% depth-of-discharge	1000	-	-	cycles
	40 °C	10% depth-of-discharge	2500	-	-	cycles
		50% depth-of-discharge	500	-	-	cycles
Recharge Time (to 80% of rated capacity; 4.1V charge; 25 °C)	Charge cycle 2	-	11	22	minutes	
	Charge cycle 1000	-	45	70		
Capacity	150nA discharge; 25 °C	5	-	-	μAh	

(1) First month recoverable self-discharge is 5% average.

(2) Storage temperature is for uncharged EnerChip™ CC device.

**Note:** All specification contained within this document are subject to change without notice.



### Functional Description of Integrated PCF8523 Real-Time Clock

The PCF8523 contains:

- 20 8-bit registers with an auto-incrementing address register
- An on-chip 32.768 kHz oscillator with two integrated load capacitors
- A frequency divider, which provides the source clock for the Real-Time Clock (RTC)
- A programmable clock output
- A 1 Mbit/s I2C-bus interface
- An offset register, which allows fine-tuning of the clock

All 20 registers are designed as addressable 8-bit registers although not all bits are implemented.

- The first three registers (memory address 00h, 01h, and 02h) are used as control and status registers
- The addresses 03h through 09h are used as counters for the clock function (seconds up to years)
- Addresses 0Ah through 0Dh define the alarm condition
- Address 0Eh defines the offset calibration
- Address 0Fh defines the clock-out mode and the addresses 10h and 12h the timer mode
- Addresses 11h and 13h are used for the timers

### Standby Mode

When the device is first powered up from the battery (VBAT) but without a main supply (VDD), the PCF8523 automatically enters the standby mode. In standby mode, the PCF8523 does not draw any power from the back up battery until the device is powered up from the main power supply VDD. Thereafter, the device switches over to battery backup mode whenever the main power supply VDD is lost.

It is also possible to enter into standby mode when the chip is already supplied by the main power supply VDD and a backup battery is connected. To enter the standby mode, the power management control bits PM[2:0] have to be set logic 111. Then the main power supply VDD must be removed. As a result of it, the PCF8523 enters the standby mode and does not draw any current from the backup battery before it is powered up again from main supply VDD.

The interface is disabled in battery backup operation:

- Interface inputs are not recognized, preventing extraneous data being written to the device
- Interface outputs are high-impedance

### PCF8523 Register Overview

The 20 registers of the PCF8523 are auto-incrementing after each read or write data byte up to register 13h. After register 13h, the auto-incrementing will wrap around to address 00h.

Bit positions labeled as ‘-’ are not implemented and will return a ‘0’ when read. Bit ‘T’ must always be written with logic ‘0’.

Address	Register name	Bit							
		7	6	5	4	3	2	1	0
<b>Control registers</b>									
00h	Control_1	CAP_SEL	T	STOP	SR	12_24	SIE	AIE	CIE
01h	Control_2	WTAF	CTAF	CTBF	SF	AF	WTAIE	CTAIE	CTBIE
02h	Control_3	PM[2:0]			-	BSF	BLF	BSIE	BLIE
<b>Time and date registers</b>									
03h	Seconds	OS	SECONDS (0 to 59)						
04h	Minutes	-	MINUTES (0 to 59)						
05h	Hours	-	-	AMPM	HOURS (1 to 12 in 12 hour mode)				
					HOURS (0 to 23 in 24 hour mode)				
06h	Days	-	-	DAYS (1 to 31)					
07h	Weekdays	-	-	-	-	-	WEEKDAYS (0 to 6)		
08h	Months	-	-	-	MONTHS (1 to 12)				
09h	Years	YEARS (0 to 99)							
<b>Alarm registers</b>									
0Ah	Minute_alarm	AE_M	MINUTE_ALARM (0 to 59)						
0Bh	Hour_alarm	AE_H	-	AMPM	HOUR_ALARM (1 to 12 in 12 hour mode)				
			-	HOUR_ALARM (0 to 23 in 24 hour mode)					
0Ch	Day_alarm	AE_D	-	DAY_ALARM (1 to 31)					
0Dh	Weekday_alarm	AE_W	-	-	-	-	WEEKDAY_ALARM (0 to 6)		
<b>Offset register</b>									
0Eh	Offset	MODE	OFFSET[6:0]						
<b>CLOCKOUT and timer registers</b>									
0Fh	Tmr_CLKOUT_ctrl	TAM	TBM	COF[2:0]			TAC[1:0]	TBC	
10h	Tmr_A_freq_ctrl	-	-	-	-	-	TAQ[2:0]		
11h	Tmr_A_reg	TIMER_A_VALUE[7:0]							
12h	Tmr_B_freq_ctrl	-	TBW[2:0]			-	TBQ[2:0]		
13h	Tmr_B_reg	TIMER_B_VALUE[7:0]							

**Power Supply Current Characteristics**
**T<sub>a</sub> = -20°C to +70°C**

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS	
Quiescent Current	I <sub>q</sub>	ENABLE=GND	V <sub>DD</sub> =3.3V	-	3.5	μA
			V <sub>DD</sub> =5.5V	-	6.0	μA
		ENABLE=V <sub>DD</sub>	V <sub>DD</sub> =3.3V	-	35	μA
			V <sub>DD</sub> =5.5V	-	38	μA
EnerChip Cutoff Current (I <sub>QBATON</sub> adds to RTC current when in backup mode)	I <sub>QBATOFF</sub>	V <sub>BAT</sub> < V <sub>BATCO</sub> , V <sub>OUT</sub> =0	-	0.5	nA	
	I <sub>QBATON</sub>	V <sub>BAT</sub> > V <sub>BATCO</sub> , ENABLE=V <sub>DD</sub> , I <sub>OUT</sub> =0	-	42	nA	

**Interface Logic Signal Characteristics**
**V<sub>DD</sub> = 2.5V to 5.5V, T<sub>a</sub> = -20°C to +70°C**

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
High Level Input Voltage	V <sub>IH</sub>	-	V <sub>DD</sub> - 0.5	-	Volts
Low Level Input Voltage	V <sub>IL</sub>	-	-	0.5	Volts
High Level Output Voltage	V <sub>OH</sub>	V <sub>DD</sub> > V <sub>TH</sub> (see Figures 4 and 5) I <sub>L</sub> =10μA	V <sub>DD</sub> - 0.04V <sup>(1)</sup>	-	Volts
Low Level Output Voltage	V <sub>OL</sub>	I <sub>L</sub> = -100μA	-	0.3	Volts
Logic Input Leakage Current	I <sub>IN</sub>	0 < V <sub>IN</sub> < V <sub>DD</sub>	-1.0	+1.0	nA

(1) RESET tracks V<sub>DD</sub>; RESET = V<sub>DD</sub> - (I<sub>OUT</sub> × R<sub>OUT</sub>).

**RESET Signal AC/DC Characteristics**
**V<sub>DD</sub> = 2.5V to 5.5V, T<sub>a</sub> = -20°C to +70°C**

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
V <sub>DD</sub> Rising to $\overline{\text{RESET}}$ Rising	t <sub>RESETH</sub>	V <sub>DD</sub> rising from 2.8V TO 3.1V in <10μs	60	200	ms
V <sub>DD</sub> Falling to $\overline{\text{RESET}}$ Falling	t <sub>RESETL</sub>	V <sub>DD</sub> falling from 3.1V to 2.8V in <100ns	0.5	2	μs
TRIP Voltage V <sub>DD</sub> Rising	V <sub>RESET</sub>	V <sub>MODE</sub> =GND	2.85	3.15	V
$\overline{\text{RESET}}$ Hysteresis Voltage <sup>(3)</sup> (V <sub>DD</sub> to $\overline{\text{RESET}}$ )	V <sub>HYST</sub>	V <sub>MODE</sub> =V <sub>DD</sub>	60	100	mV
		V <sub>MODE</sub> =GND	45	75	
		V <sub>MODE</sub> = V <sub>DD</sub> /2	30	50	

(2) Users- selectable trip voltage can be set by placing a resistor divider from the V<sub>MODE</sub> pin to GND. Refer to Figure 8.

(3) The Hysteresis is a function of trip level in Mode 2. Refer to Figure 9.

**Charge Pump Characteristics**
 $V_{DD} = 2.5V \text{ to } 5.5V, T_a = -20^{\circ}C \text{ to } +70^{\circ}C$ 

CHARACTERISTIC	SYMBOL	CONDITION	MIN	MAX	UNITS
ENABLE= $V_{DD}$ to Charge Pump Active	$t_{CPON}$	ENABLE to 3rd charge pump pulse, $V_{DD}=3.3V$	60	80	$\mu s$
ENABLE Falling to Charge Pump Inactive	$t_{CPOFF}$	-	0	1	$\mu s$
Charge Pump Frequency	$f_{CP}$		-	120	KHz <sup>(1)</sup>
Charge Pump Resistance	$R_{CP}$	Delta $V_{BAT}$ , for $I_{BAT}$ charging current of $1\mu A$ to $100\mu A$ $C_{FLY}=0.1\mu F, C_{BAT}=1.0\mu F$	150	300	$\Omega$
$V_{CHG}$ Output Voltage	$V_{CP}$	$C_{FLY}=0.1\mu F, C_{BAT}=1.0\mu F, I_{OUT}=1\mu A, Temp=+25^{\circ}C$	4.075	4.125	V
$V_{CHG}$ Temp. Coefficient	$T_{CCP}$	$I_{OUT}=1\mu A, Temp=+25^{\circ}C$	-2.0	-2.4	mV/ $^{\circ}C$
Charge Pump Current Drive	$I_{CP}$	$I_{BAT}=1mA$ $C_{FLY}=0.1\mu F, C_{BAT}=1.0\mu F$	1.0	-	mA
Charge Pump on Voltage	$V_{ENABLE}$	ENABLE= $V_{DD}$	2.5	-	V

 $(1) f_{cp} = 1/t_{CPPER}$ 
**Additional Characteristics**
 $T_a = -20^{\circ}C \text{ to } +70^{\circ}C$ 

CHARACTERISTIC	SYMBOL	CONDITION	LIMITS		UNITS
			MIN	MAX	
$V_{BAT}$ Cutoff Threshold	$V_{BATCO}$	$I_{OUT}=1\mu A$	2.75	3.25	V
Cutoff Temp. Coefficient	$T_{CCO}$	-	+1	+2	mV/ $^{\circ}C$
$V_{BAT}$ Cutoff Delay Time	$t_{CCOFF}$	$V_{BAT}$ from 40mV above to 20mV below $V_{BATCO}$ $I_{OUT}=1\mu A$	40	-	ms

**Note: All specification contained within this document are subject to change without notice.**

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